AMENDMENTS TO THE CLAIMS ARE AS FOLLOWS:

What is claimed is:

1. (CURRENTLY AMENDED). A method of forming a semiconductor device, the steps comprising:

forming a silicon dioxide layer on a semiconductor substrate;

forming a silicon nitride layer on said silicon dioxide layer;

forming isolation trench regions in said semiconductor substrate;

removing said silicon nitride layer;

first blanket implantation of dopant through said silicon dioxide to form sacrificial blanket implanted silicon dioxide layer;

second blanket implantation of dopant through said sacrificial blanket implanted silicon dioxide layer to form wells; and

removing said sacrificial blanket implanted silicon dioxide layer and forming a gate dielectric layer over said semiconductor substrate.

2. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim **1**, wherein said silicon dioxide layer thickness is approximately about 25 Å - 120 Å.

3. (CURRENTLY AMENDED). The method of forming a semiconductor device according to claim **1**, wherein said first blanket implanted dopant comprises n- or p- type ions.

4. (CURRENTLY AMENDED). The method of forming a semiconductor device according to claim **3**, wherein said first blanket implanted n- type dopant is As^+ or P^+ ion.

5. (CURRENTLY AMENDED). The method of forming a semiconductor device according to claim **4**, wherein said blanket implanted As^+ dopant implantation energy, dose, and tilt angle are approximately about 2 – 7 keV, 3E11 – 7E11 ions/cm^2, and 5 – 10 degrees of tilt angle respectively; and for P^+ ion, implant energy, dose and tilt angle are approximately about 2 – 15 keV, 3E11 – 7E11 ions/cm^2, and 5 – 10 degrees respectively.

6. (CURRENTLY AMENDED). The method of forming a semiconductor device according to claim **1**, wherein said second blanket implanted dopant comprises n- or p- type ions.

7. (CURRENTLY AMENDED). The method of forming a semiconductor device according to claim **6**, wherein said second blanket implanted n- type dopant is As^+ or P^+ ion.

8. (CURRENTLY AMENDED). The method of forming a semiconductor device according to claim **7**, wherein said second blanket implanted As^+ or P^+ ion dopant implantation energy, dose, and tilt angle are approximately about 80 – 140 keV, 1E13 – 2E13 ions/cm^2, and 0 – 15 degrees of tilt angle respectively.

9. (PREVIOUSLY PRESENTED). A method of forming a semiconductor device, the steps comprising:

forming a silicon dioxide layer on a silicon substrate;

forming a silicon nitride layer on said silicon dioxide layer;

forming isolation trench regions in said silicon substrate and removing said silicon nitride;

first implantation of As^+ dopant through said silicon dioxide layer to form sacrificial implanted silicon dioxide layer;

second implantation of As^+ dopant through said sacrificial implanted silicon dioxide layer to form wells; and

removing said sacrificial implanted silicon dioxide layer and forming a gate dielectric layer over said silicon substrate.

10. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim **9**, wherein said silicon dioxide layer thickness is approximately about 25 Å - 120 Å.

11. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim **9**, wherein said first implanted As^+ dopant implantation energy, dose, and tilt angle are approximately about 2-7 keV, 3E11– 7E11 ions/cm^2, and 5 – 10 degrees of tilt angle respectively.

12. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim **9**, wherein said second implanted As^+ dopant implantation energy, dose, and tilt angle are approximately about 80 - 140 keV, 1E13 – 2E13 ions/cm^2, and 0 - 15 degrees of tilt angle respectively.

13. (PREVIOUSLY PRESENTED). A method of forming a semiconductor device with improved threshold voltage stability, the steps comprising:

forming isolation trenches in a silicon substrate with steps comprising: forming silicon nitride over silicon dioxide stack on said silicon substrate; and selective removal of said silicon nitride;

forming a sacrificial implanted silicon dioxide layer by implanting first As^+ ions into said silicon dioxide layer;

forming n- well in silicon substrate by second implantation of As^+ ions through said sacrificial implanted silicon dioxide layer; and

removing said sacrificial implanted silicon dioxide layer and forming a gate dielectric layer over said silicon substrate.

14. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim **13**, wherein said silicon dioxide layer thickness is approximately about 25 Å - 120 Å.

15. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim **13**, wherein said first implanted As^+ dopant implantation energy, ion dose, and tilt angle are approximately about 2 - 7 keV, 3E11 – 7E11 ions/cm^2, and 5 – 10 degrees of tilt angle respectively.

16. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim **13**, wherein said second implanted As^+ dopant implantation energy,

dose, and tilt angle are approximately about 80 - 140 keV, 1E13 – 2E13 ions/cm^2, and 0 - 15 degrees of tilt angle respectively.